

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) An electro-optical device comprising, above a substrate:
a data lines-line extending in a first direction;
a scanning lines-line extending in a second direction and intersecting the data
~~lines; line;~~
a pixel electrodes-electrode and a thin film transistors-transistor disposed so as
to correspond to an intersection regions-region of the data ~~lines-line~~ and the scanning
~~lines;line;~~
a storage eapacitors-capacitor electrically connected to the thin film ~~transistors~~
~~transistor~~ and the pixel ~~electrodes; electrode;~~ and
a shielding layers-layer disposed between the data ~~lines-line~~ and the pixel
~~electrodes;electrode,~~
a nitride films-film being included in the shielding ~~layers-layer~~ and ~~are-being~~
formed along the data ~~lines-line~~ and ~~being-wider~~ than the data ~~lines- line.~~
2. (Currently Amended) The electro-optical device according to Claim 1, a
planarization process being performed on ~~the surfaces-a surface~~ of an interlayer insulating
~~films-film~~ arranged as ~~the bases-a base~~ of the pixel ~~electrodes- electrode.~~
3. (Currently Amended) The electro-optical device according to Claim 1, ~~each-of~~
the data ~~lines-line~~ being formed of the same film as one of a pair of electrodes which
constitute ~~each-of-the~~ a storage-capacitors- capacitor.
4. (Currently Amended) The electro-optical device according to Claim 3, the
data ~~lines-line~~ forming a laminated structure of an aluminum film and a conductive
polysilicon film.

5. (Currently Amended) The electro-optical device according to Claim 1, further comprising:

a relay ~~layers-layer~~ being electrically connected to the pixel ~~electrodes~~
electrode and one of a pair of electrodes which constitute ~~each of the~~ a storage capacitors-
capacitor.

6. (Currently Amended) The electro-optical device according to Claim 5, the
relay ~~layers-layer~~ being made of an aluminum ~~films-film~~ and a nitride ~~films-~~ film.

7. (Currently Amended) The electro-optical device according to Claim 5, the
shielding ~~layers-layer~~ being formed of the same films-film as the relay ~~layers-~~ layer.

8. (Currently Amended) The electro-optical device according to Claim 1, the
nitride ~~films-film~~ being formed on ~~the surfaces~~ a surface of the data ~~lines-~~ line.

9. (Withdrawn-Currently Amended) An electro-optical device comprising, above
a substrate:

a data ~~lines-line~~ extending in a first direction;

a scanning ~~lines-line~~ extending in a second direction and intersecting the data
~~lines;~~ line;

a pixel ~~electrodes-electrode~~ and a thin film ~~transistors-transistor~~ disposed so as
to correspond to an intersection ~~regions-region~~ of the data ~~lines-line~~ and the scanning ~~lines-~~
line;

a storage ~~capacitors-capacitor~~ electrically connected to the thin film ~~transistors~~
transistor and the pixel ~~electrodes;~~ electrode; and

a shielding ~~layers-layer~~ disposed between the data ~~lines-line~~ and the pixel
~~electrodes;~~ electrode.

a nitride ~~films-film~~ being included in the data ~~lines-line.~~

10. (Withdrawn-Currently Amended) The electro-optical device according to Claim 9, the nitride ~~films~~ film being formed in ~~regions-a region~~ where the scanning ~~lines~~ extend, line extends.

11. (Withdrawn-Currently Amended) The electro-optical device according to Claim 9, the nitride ~~films~~ film being formed around an image display ~~regions-region~~ defined as ~~regions-a region~~ where the pixel ~~electrodes~~, electrode, the data ~~lines~~, line and the scanning ~~lines~~ line are formed.

12. (Withdrawn-Currently Amended) The electro-optical device according to Claim 9, the nitride ~~films~~ film formed on the data ~~lines~~ line being wider than the data ~~lines~~, line.

13. (Withdrawn-Currently Amended) The electro-optical device according to Claim 12, each of the ~~edges~~ edge of the nitride ~~films~~ film being larger than each of the ~~edges~~ edge of the data ~~lines~~ line by 0.1 to 2.2 μm .

14. (Withdrawn-Currently Amended) The electro-optical device according to Claim 9, the thickness of the nitride ~~films~~ film being 10 to 100 nm.

15. (Withdrawn-Currently Amended) The electro-optical device according to Claim 9, further comprising:

another substrate that faces the substrate with an electro-optical material interposed therebetween and a light-shielding ~~films~~ film formed on the other substrate so as to correspond to the scanning ~~lines~~ line and the data ~~lines~~, line,

the nitride ~~films~~ film being narrower than the light-shielding ~~films~~, film.

16. (Withdrawn-Currently Amended) The electro-optical device according to Claim 15, each of the ~~edges~~ edge of the nitride ~~films~~ film being smaller than each of the ~~edges~~ edge of the light-shielding ~~films~~ film by up to 1 μm .

17. (Withdrawn-Currently Amended) The electro-optical device according to Claim 9, further comprising:

another substrate that faces the substrate with an electro-optical material interposed therebetween and a light-shielding films-film formed on the other substrate so as to correspond to the scanning lines-line and the data lines, line,

the nitride films-film being wider than the light-shielding films. film.

18. (Currently Amended) The electro-optical device according to Claim 1, the shielding layers-layer being formed of a transparent conductive material and are-being formed over the-an entire surface of the substrate.

19. (Withdrawn-Currently Amended) The electro-optical device according to Claim 9, the shielding layers-layer being formed of a transparent conductive material and being formed over the entire surface of the substrate in a mat shape.

20. (Withdrawn-Currently Amended) An electro-optical device comprising, above a substrate:

a data lines-line extending in a first direction;

a scanning lines-line extending in a second direction and intersecting the data lines; line;

a pixel electrodes-electrode and a thin film transistors-transistor disposed so as to correspond to an intersection regions-region of the data lines-line and the scanning lines; line;

a storage capacitors-capacitor electrically connected to the thin film transistors transistor and the pixel electrodes; electrode; and

a shielding layers-layer disposed between the data lines-line and the pixel electrodes; electrode.

a dielectric films-film which constitute-constitutes the storage capacitors
capacitor being made of a plurality of layers including different materials and one of the
plurality of the layers being made of a material having a higher dielectric constant than those
of the other layers, and

a nitride films-film being included in the data-lines- line.

21. (Currently Amended) An electronic apparatus having an electro-optical device
comprising, above a substrate:

a data lines-line extending in a first direction;

a scanning lines-line extending in a second direction and intersecting the data
lines; line;

a pixel electrodes-electrode and a thin film transistors-transistor disposed so as
to correspond to an intersection regions-region of the data lines-line and the scanning-lines;
line, the thin film transistor including a semiconductor layer;

a storage capacitors-capacitor electrically connected to the thin film transistors
transistor and the pixel-electrodes; electrode;

a relay layer electrically connected with the pixel electrode;

a first contact hole electrically connecting the semiconductor layer of the thin
film transistor with the data line;

a second contact hole electrically connecting the semiconductor layer of the
thin film transistor with the relay layer; and

a shielding layers-layer disposed between the data lines-line and the pixel
electrodes; electrode,

a nitride films-film being included in the shielding layers-layer and are-being
formed along the data lines-line and wider than the data-lines- line, the shielding layer being
formed to cover the first contact hole and the second contact hole as viewed in plan.